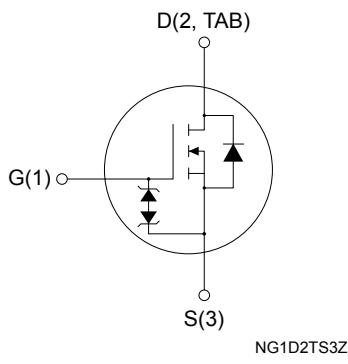
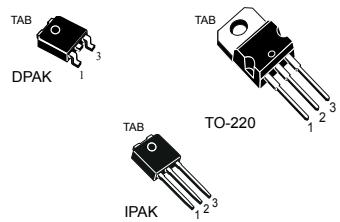


N-channel 650 V, 0.60 Ω typ., 7 A MDmesh™ M2 Power MOSFET in DPAK, TO-220 and IPAK packages



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}	Package
STD11N65M2	650 V	0.68 Ω	7 A	85 W	DPAK
STP11N65M2					TO-220
STU11N65M2					IPAK

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the MDmesh M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.



Product status link
STD11N65M2
STP11N65M2
STU11N65M2

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at $T_{case} = 25^\circ\text{C}$	7	A
	Drain current (continuous) at $T_{case} = 100^\circ\text{C}$	4.4	
$I_{DM}^{(1)}$	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at $T_{case} = 25^\circ\text{C}$	85	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by T_{jmax} .
2. $I_{SD} \leq 7 \text{ A}$, $di/dt \leq 400 \text{ A}/\mu\text{s}$, V_{DS} (peak) $\leq V_{(BR)DSS}$, $V_{DS} = 400 \text{ V}$
3. $V_{DS} \leq 520 \text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case	1.47			$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	100	
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50			

1. When mounted on a 1-inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	1.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ

1. Pulse width limited by T_{jmax} .
2. starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50 \text{ V}$.

2

Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 1 mA	650			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 650 V			1	μA
		V _{GS} = 0 V, V _{DS} = 650 V, T _{case} = 125 °C ⁽¹⁾			100	
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V			±10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 3.5 A		0.60	0.68	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V	-	410	-	pF
C _{oss}	Output capacitance		-	20	-	
C _{rss}	Reverse transfer capacitance		-	0.9	-	
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V _{DS} = 0 to 520 V, V _{GS} = 0 V	-	43	-	pF
R _G	Intrinsic gate resistance	f = 1 MHz, I _D = 0 A	-	6.4	-	Ω
Q _g	Total gate charge	V _{DD} = 520 V, I _D = 7 A, V _{GS} = 0 to 10 V (see Figure 16)	-	12.5	-	nC
Q _{gs}	Gate-source charge		-	3.2	-	
Q _{gd}	Gate-drain charge		-	5.8	-	

1. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 325 V, I _D = 3.5 A R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 15 and Figure 20)	-	9.5	-	ns
t _r	Rise time		-	7.5	-	
t _{d(off)}	Turn-off delay time		-	26	-	
t _f	Fall time		-	15	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		28	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0 \text{ V}$, $I_{SD} = 7 \text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 7 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$ (see Figure 17)	-	318		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current		-	15.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 7 \text{ A}$, $dI/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 60 \text{ V}$, $T_j = 150^\circ\text{C}$ (see Figure 17)	-	437		ns
Q_{rr}	Reverse recovery charge		-	3.2		μC
I_{RRM}	Reverse recovery current		-	15		A

1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for DPAK and IPAK

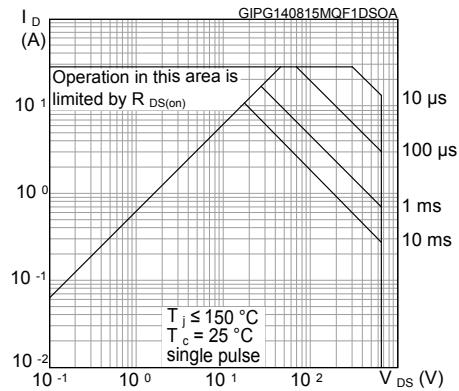


Figure 2. Thermal impedance for DPAK and IPAK

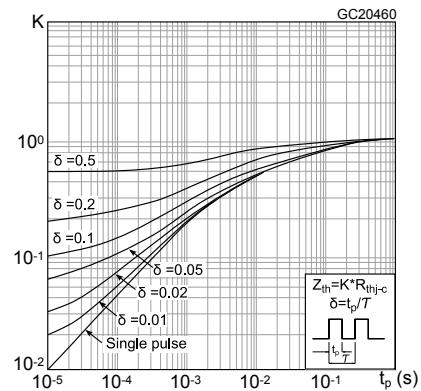


Figure 3. Safe operating area for TO-220

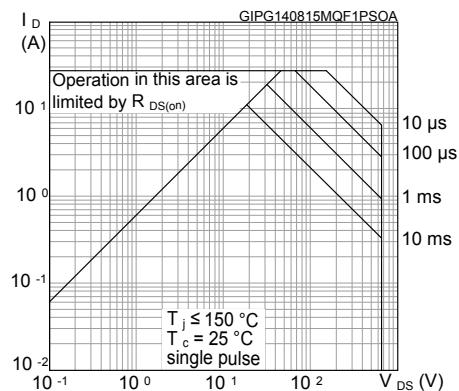


Figure 4. Thermal impedance for TO-220

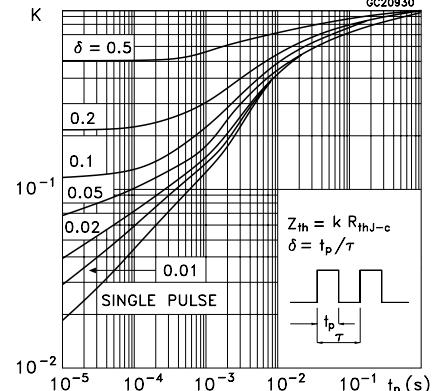


Figure 5. Output characteristics

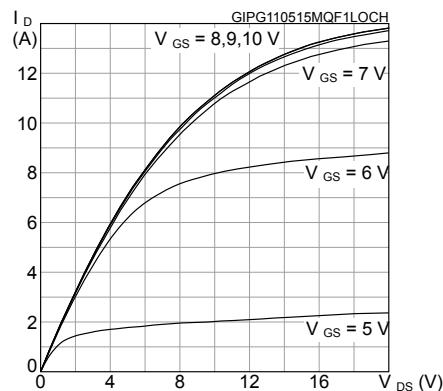


Figure 6. Transfer characteristics

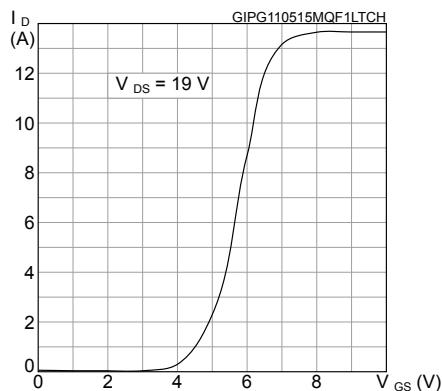


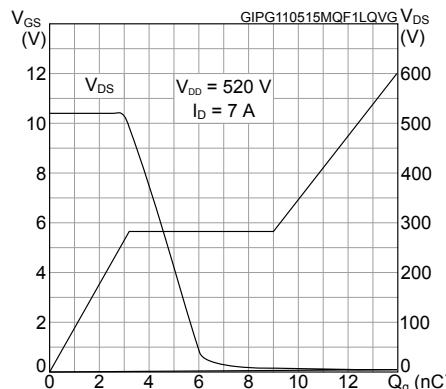
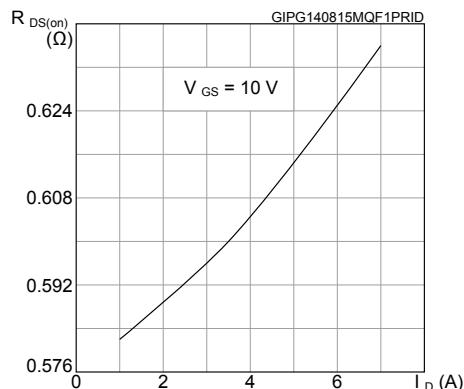
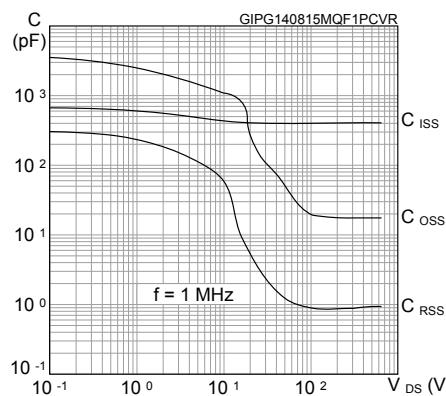
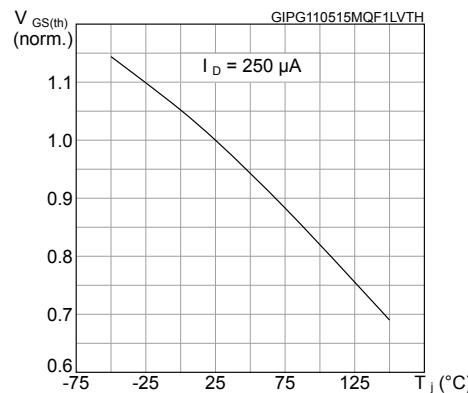
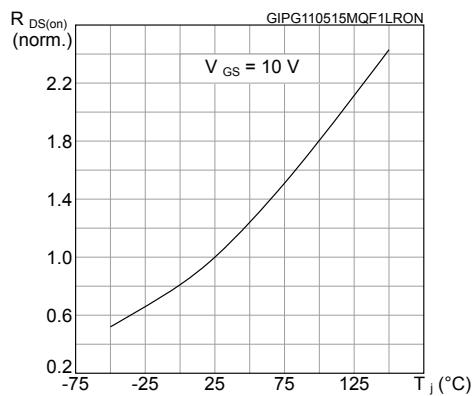
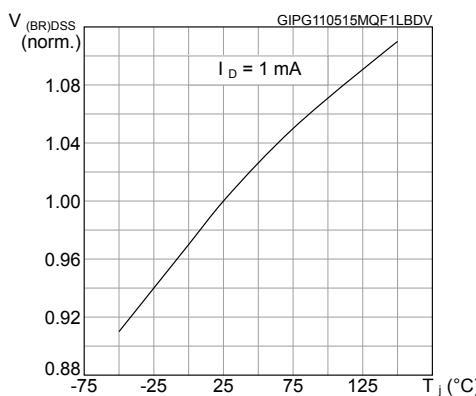
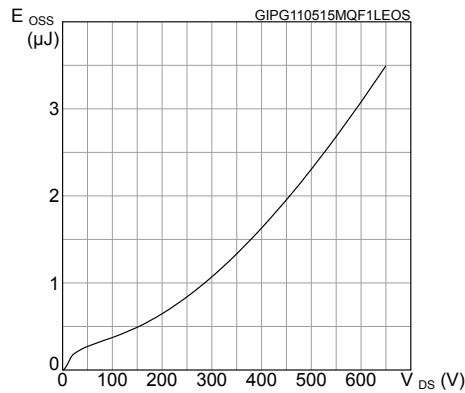
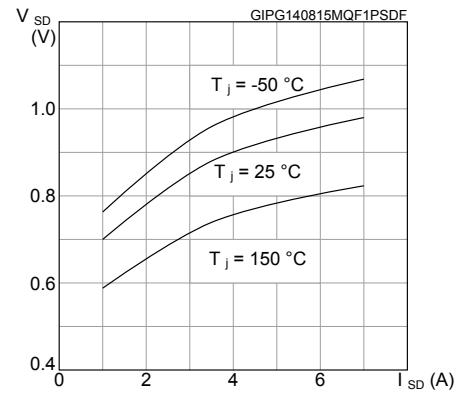
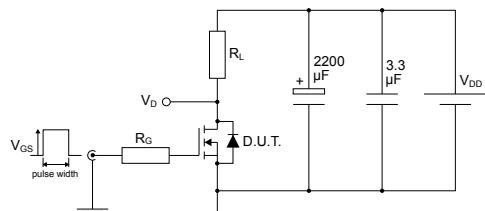
Figure 7. Gate charge vs gate-source voltage

Figure 8. Static drain-source on-resistance

Figure 9. Capacitance variations

Figure 10. Normalized gate threshold voltage vs temperature

Figure 11. Normalized on-resistance vs temperature

Figure 12. Normalized V(BR)DSS vs temperature


Figure 13. Output capacitance stored energy**Figure 14. Source- drain diode forward characteristics**

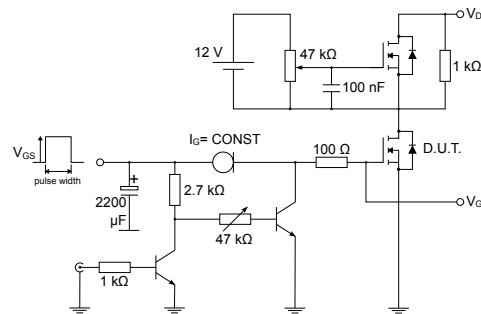
3 Test circuits

Figure 15. Test circuit for resistive load switching times



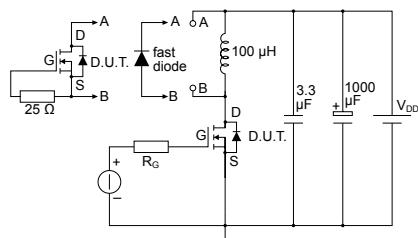
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Figure 16. Test circuit for gate charge behavior



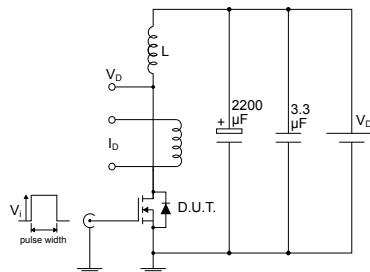
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Figure 17. Test circuit for inductive load switching and diode recovery times



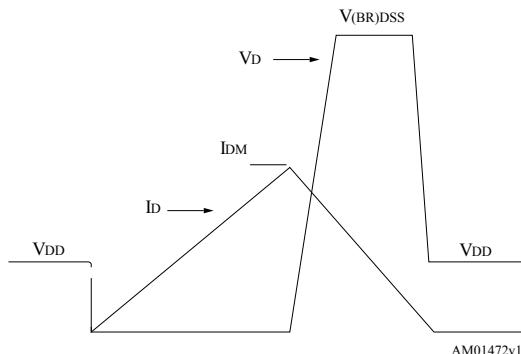
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Figure 18. Unclamped inductive load test circuit



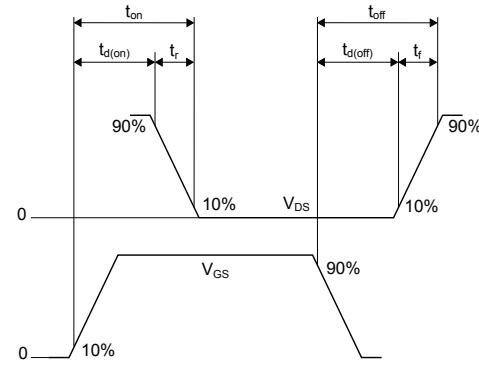
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Figure 19. Unclamped inductive waveform



AM01472v1

Figure 20. Switching time waveform



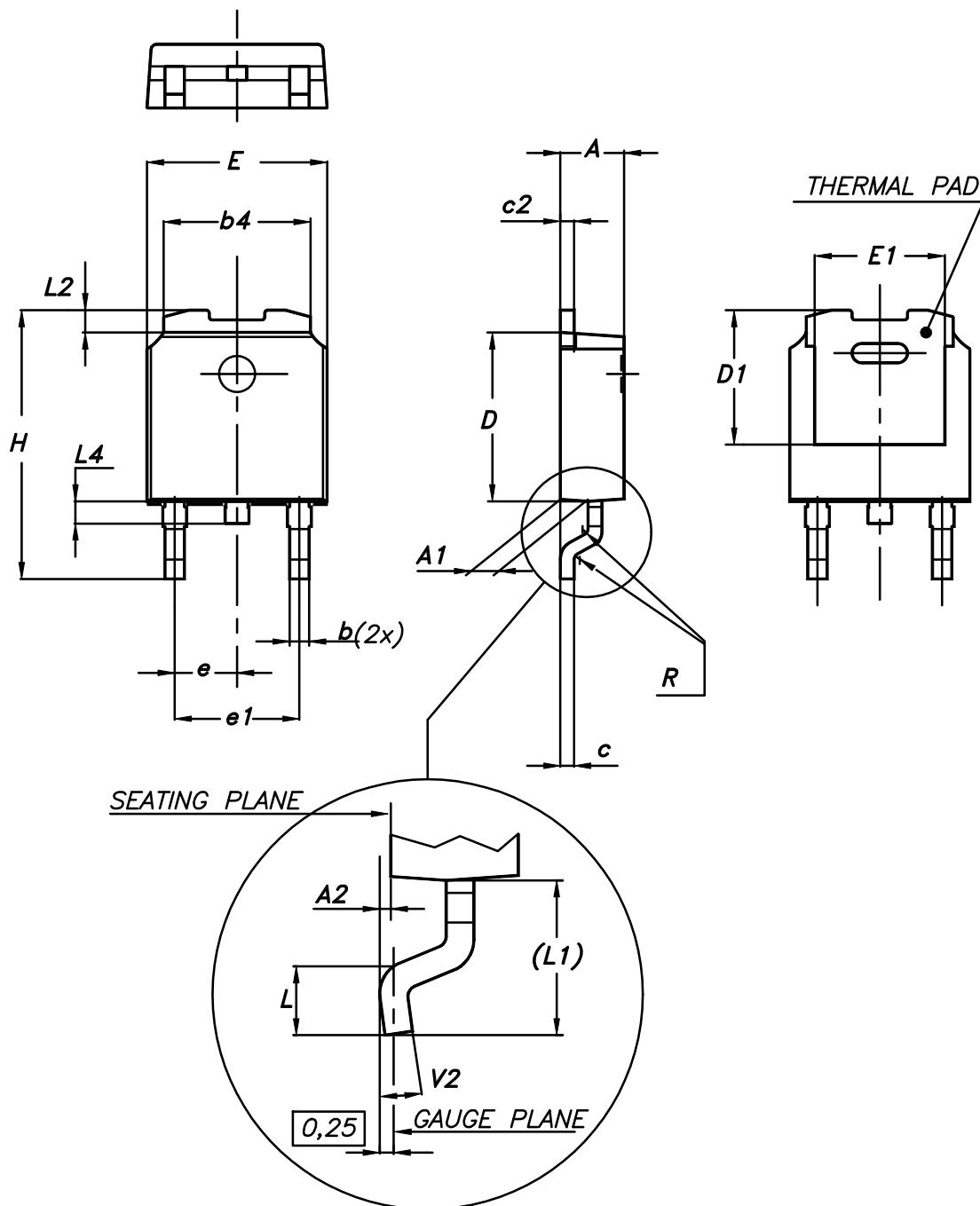
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 21. DPAK (TO-252) type A package outline



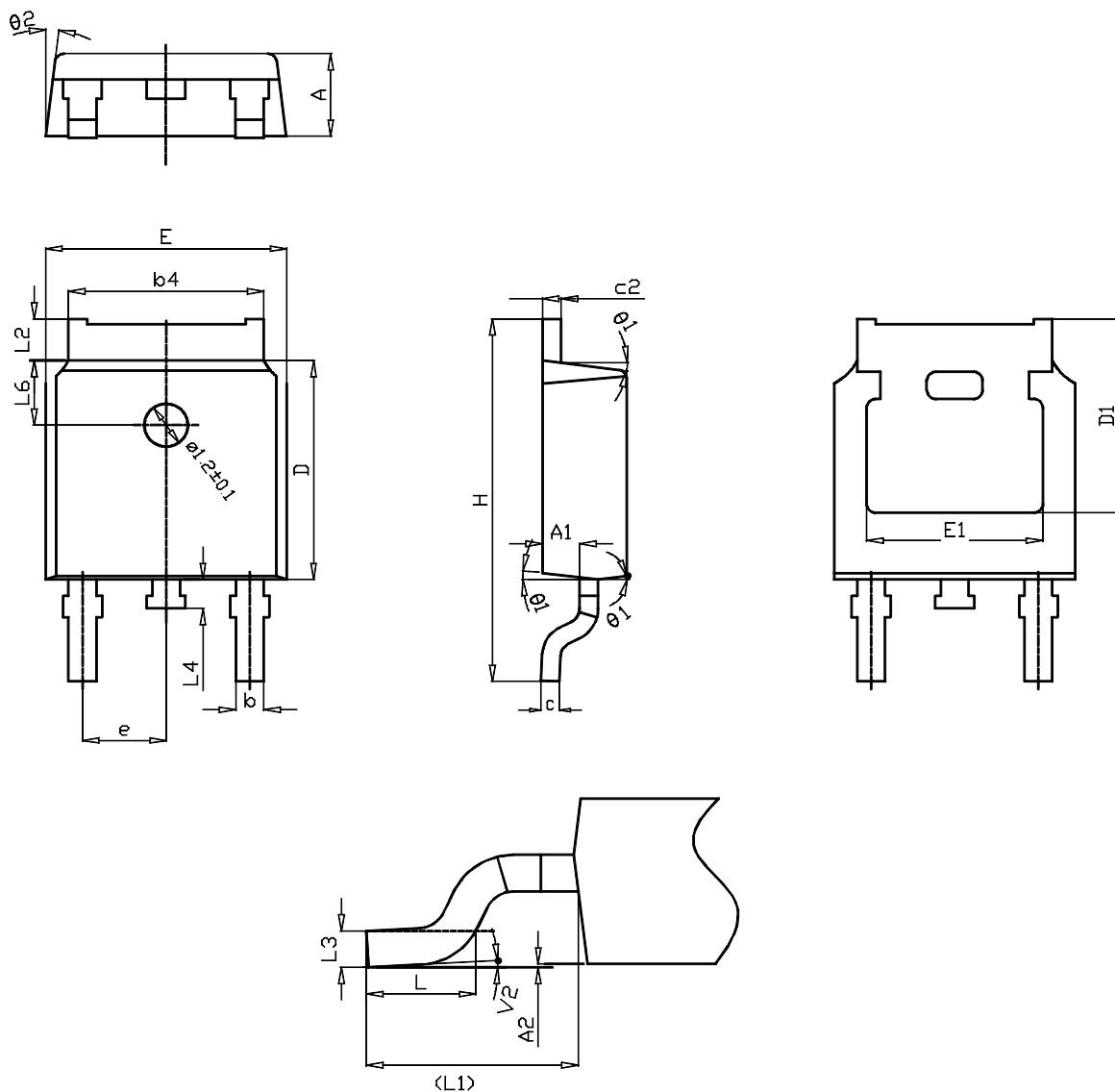
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Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C package information

Figure 22. DPAK (TO-252) type C package outline



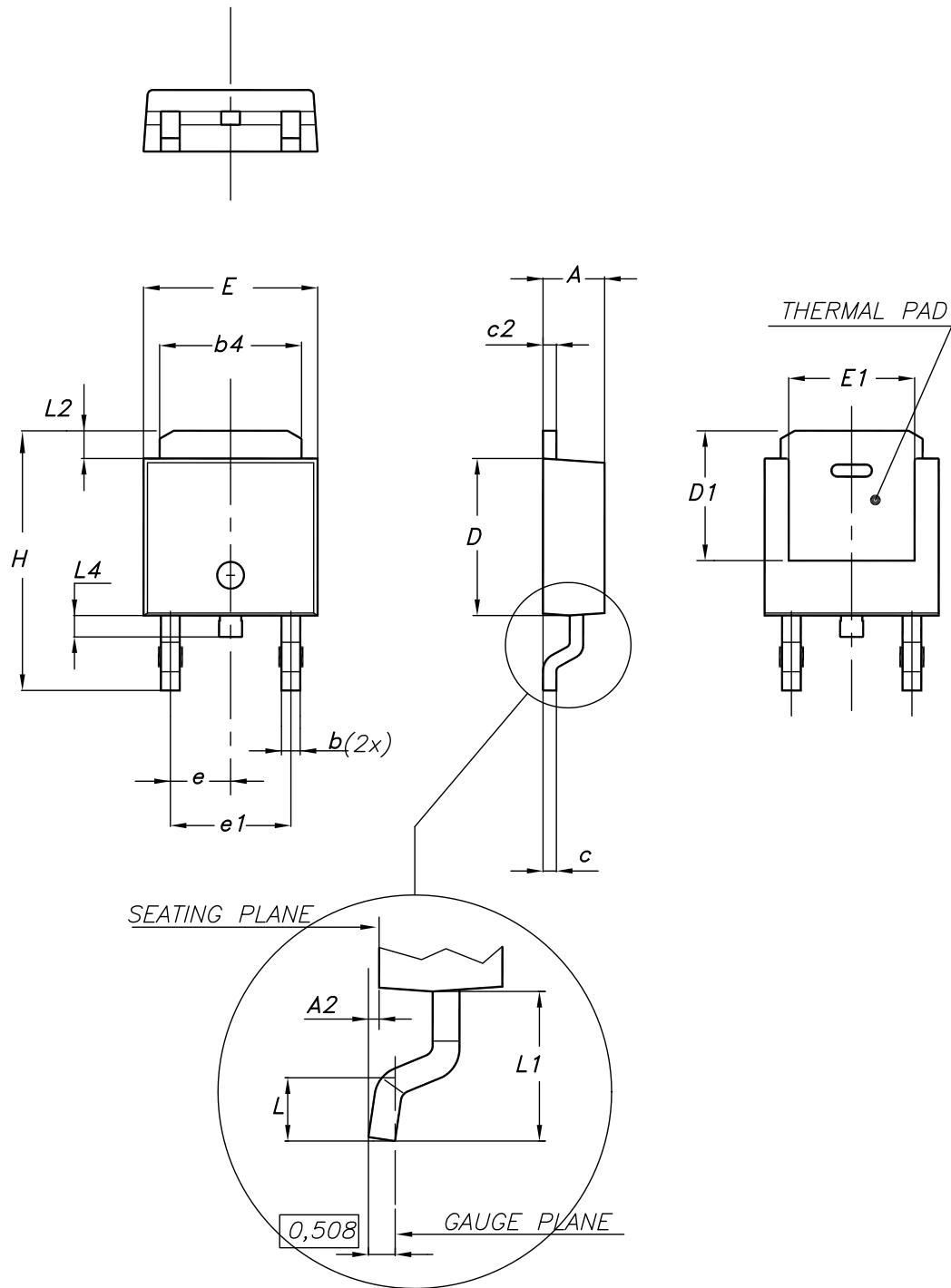
0068772_C_26

Table 9. DPAK (TO-252) type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.3 DPAK (TO-252) type E package information

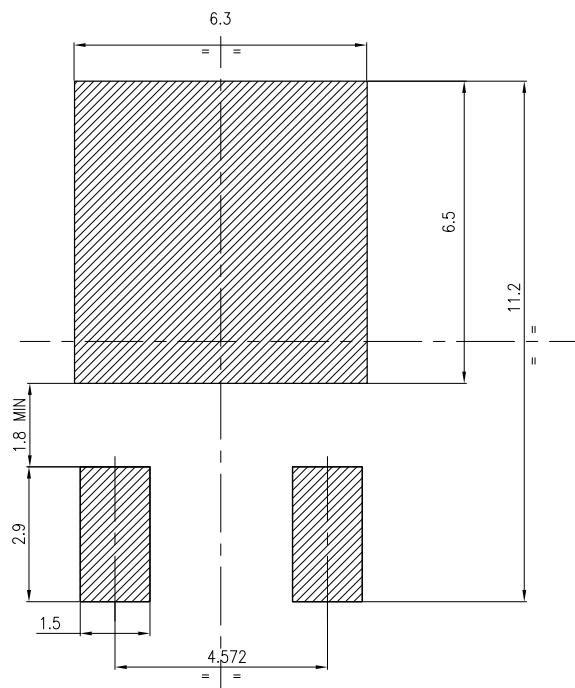
Figure 23. DPAK (TO-252) type E package outline



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Table 10. DPAK (TO-252) type E mechanical data

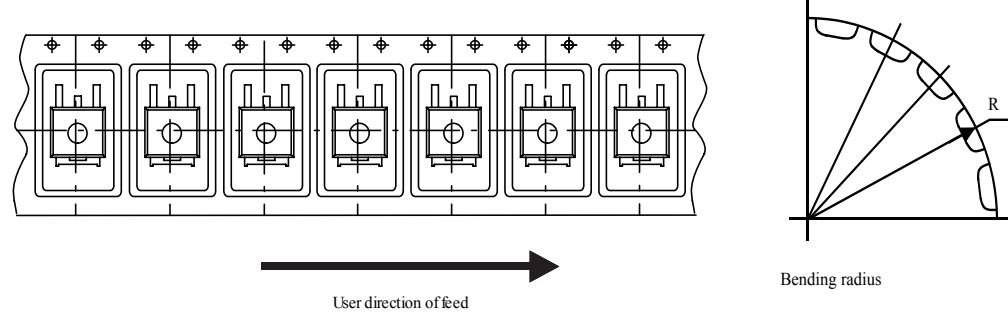
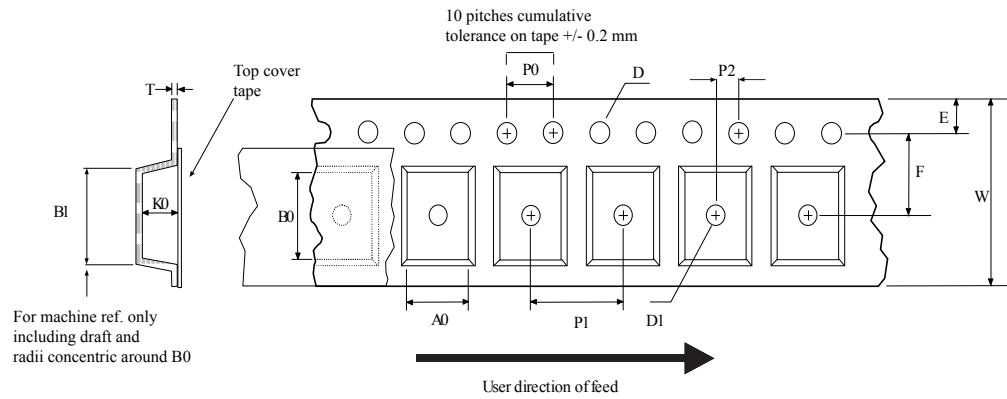
Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 24. DPAK (TO-252) recommended footprint (dimensions are in mm)


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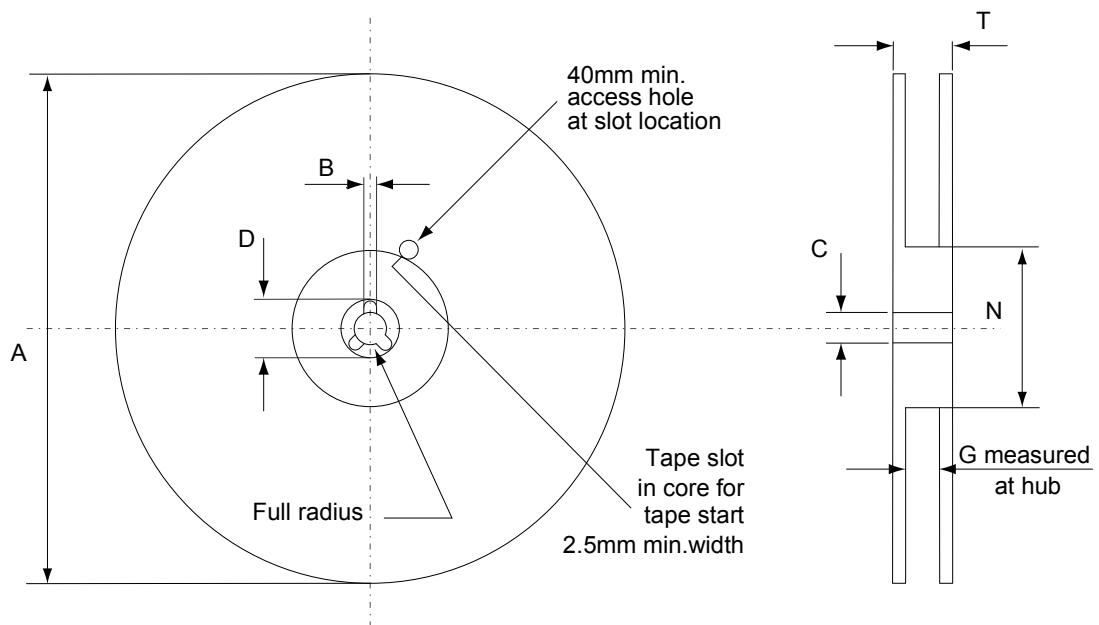
4.4 DPAK (TO-252) packing information

Figure 25. DPAK (TO-252) tape outline



Bending radius

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Figure 26. DPAK (TO-252) reel outline


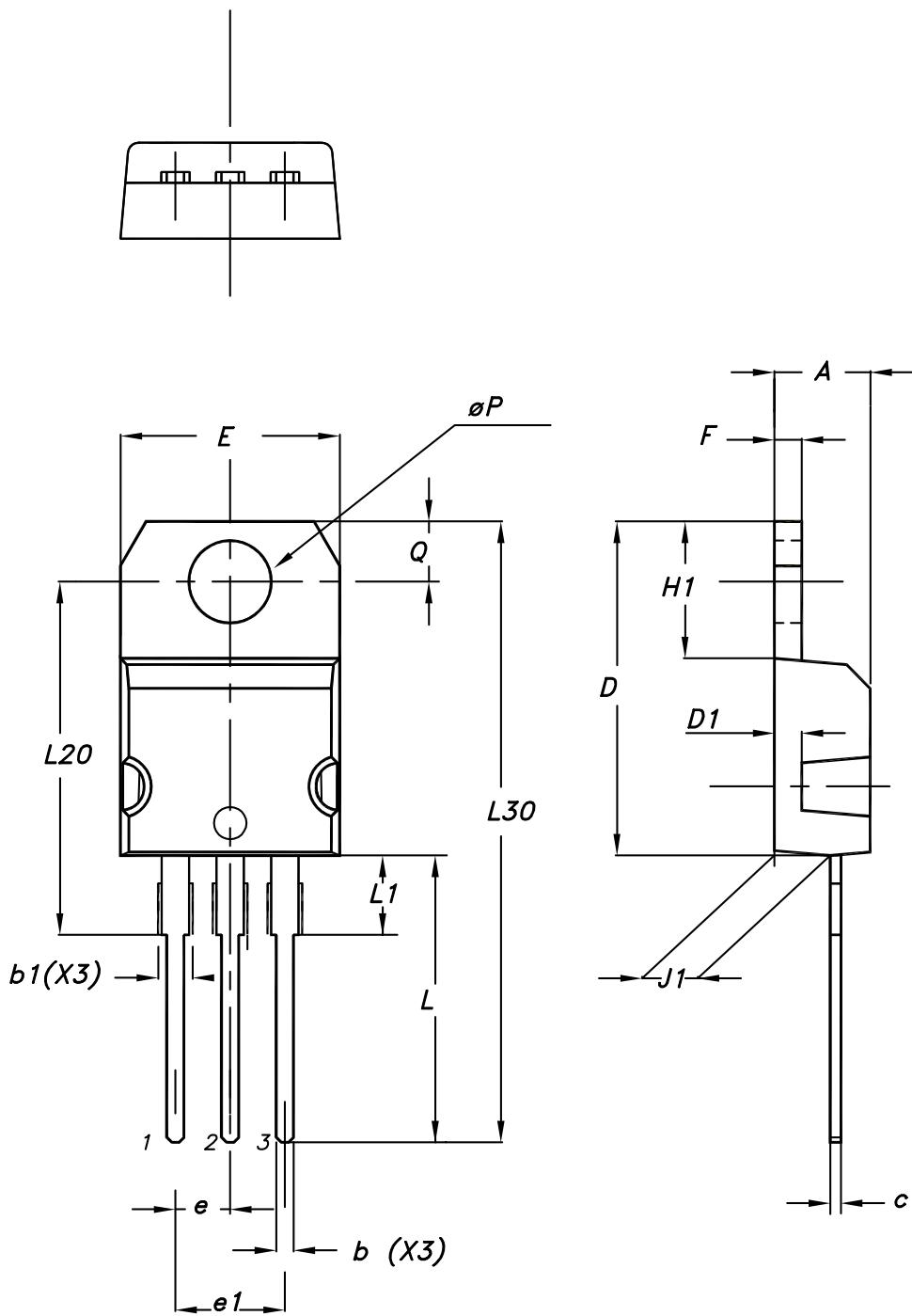
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Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220 type A package information

Figure 27. TO-220 type A package outline



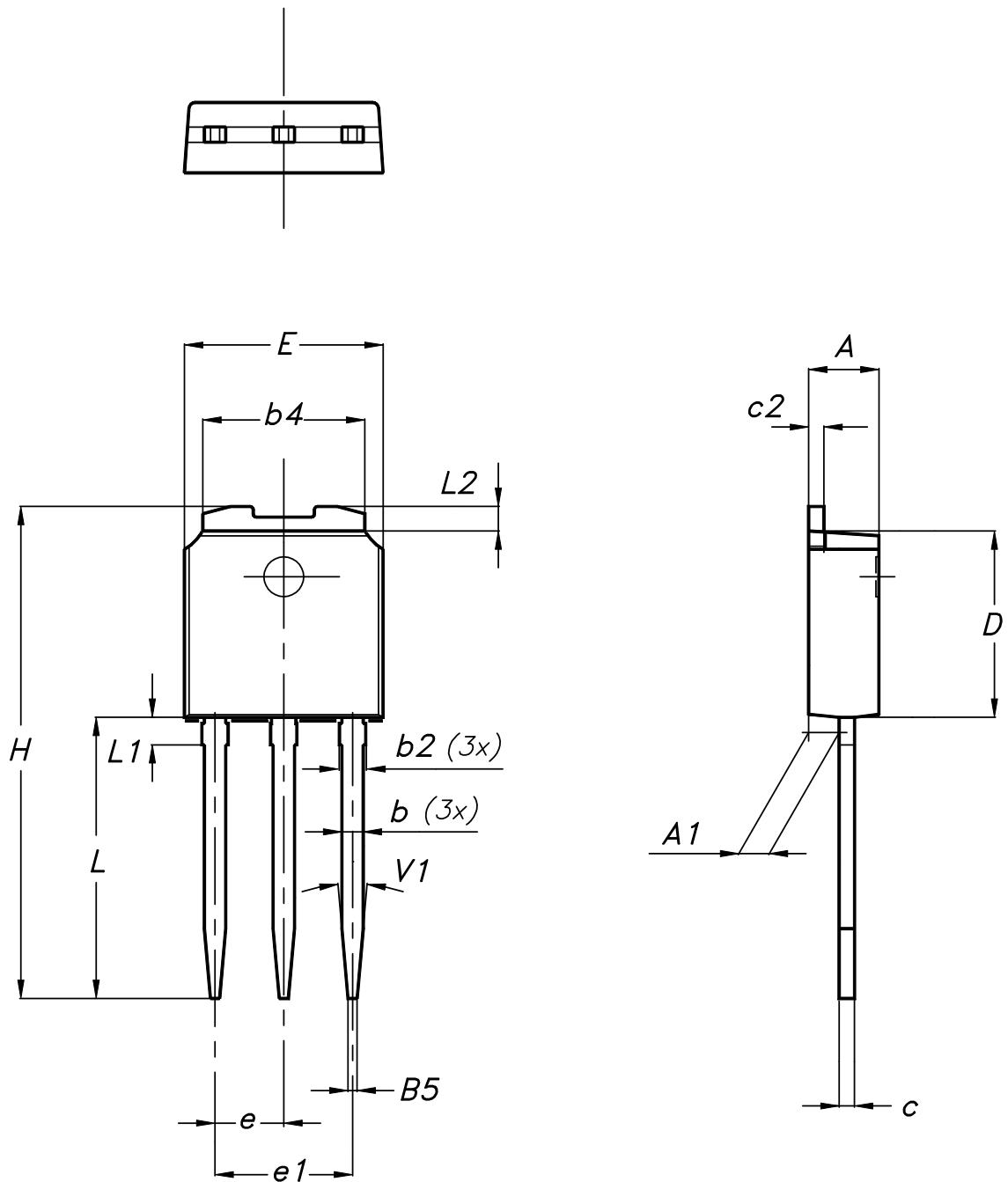
0015988_typeA_Rev_22

Table 12. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.6 IPAK (TO-251) type A package information

Figure 28. IPAK (TO-251) type A package outline



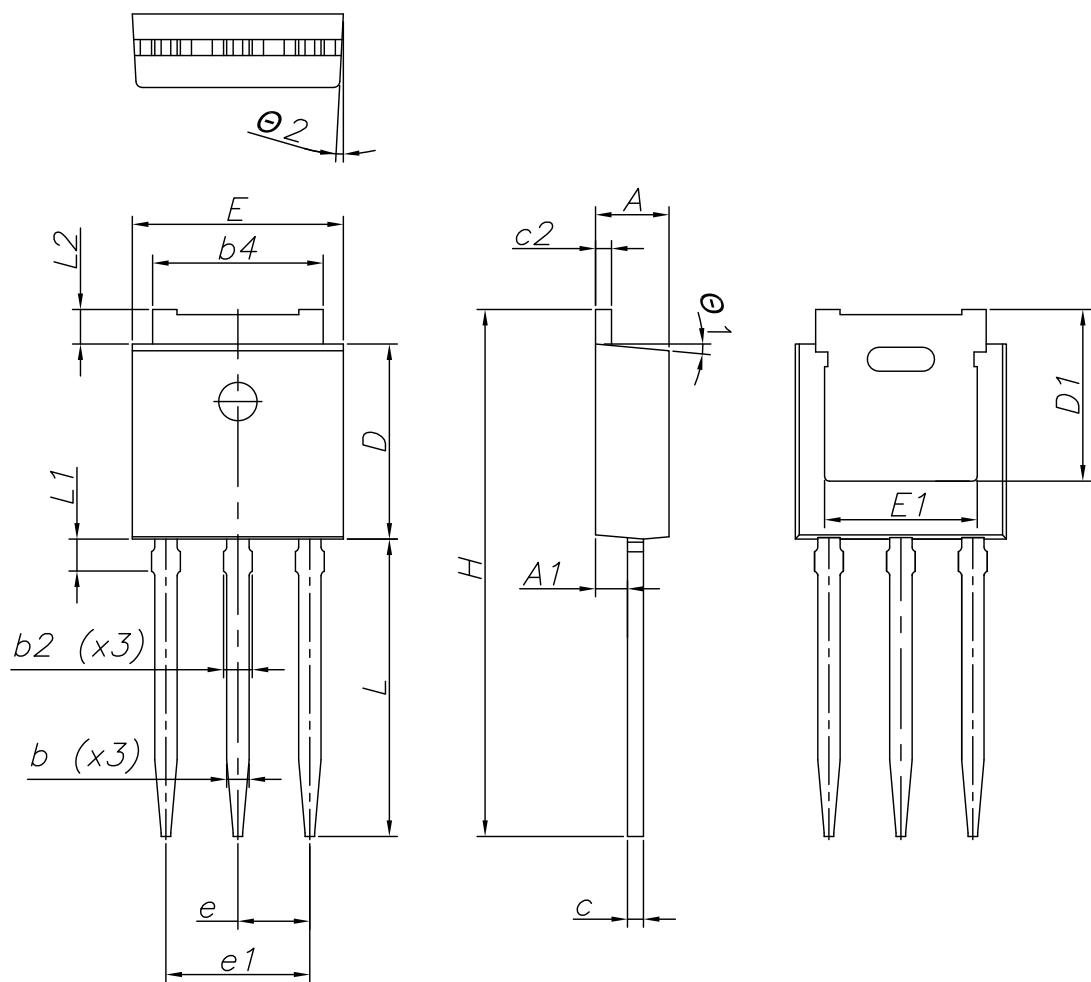
0068771_IK_typeA_rev14

Table 13. IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.7 IPAK (TO-251) type C package information

Figure 29. IPAK (TO-251) type C package outline



0068771_IK_typeC_rev14

Table 14. IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Ordering information

Table 15. Ordering information

Order code	Marking	Package	Packing
STD11N65M2	11N65M2	DPAK	Tape and reel
STP11N65M2		TO-220	Tube
STU11N65M2		IPAK	

Revision history

Table 16. Document revision history

Date	Revision	Changes
16-May-2014	1	First release.
14-Aug-2015	2	<p>Text and formatting changes throughout document.</p> <p>On cover page:</p> <ul style="list-style-type: none">- updated <i>Title, Features and Description</i> <p>In section <i>Electrical characteristics</i>:</p> <ul style="list-style-type: none">- updated and renamed table <i>Static</i> (was On /off states) <p>Updated section <i>Electrical characteristics (curves)</i></p> <p>Updated and renamed section <i>Package information</i> (was Package mechanical data)</p>
17-Aug-2015	3	<p>Datasheet promoted from preliminary data to production data.</p> <p>In section <i>Electrical ratings</i>:</p> <ul style="list-style-type: none">- updated and renamed table <i>Absolute maximum ratings</i> <p>In section <i>Electrical characteristics</i>:</p> <ul style="list-style-type: none">- updated table <i>Source-drain diode</i> <p>In section <i>Electrical characteristics (curves)</i></p> <ul style="list-style-type: none">- updated figure <i>Thermal impedance for DPAK and IPAK</i> <p>Updated and renamed section <i>IPAK (TO-251) Type C package information</i> (was IPAK (TO-251) Type A package information)</p>
07-Sep-2015	4	Minor text and formatting changes throughout document.
16-Oct-2018	5	Updated Section 4 Package information . Minor text changes.
18-Jun-2019	6	Updated Section 3 Minor text changes.

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Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литер Н,
помещение 100-Н Офис 331